Octal 3-State Noninverting Buffer/Line Driver/Line Receiver with LSTTL-Compatible Inputs

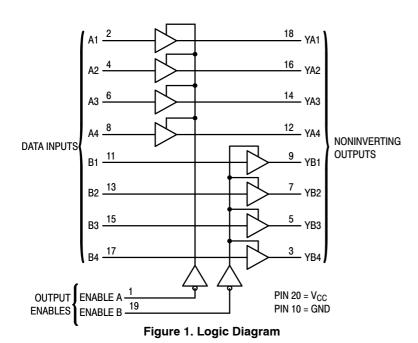
High-Performance Silicon-Gate CMOS

The MC74HCT244A is identical in pinout to the LS244. This device may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT244A is an octal noninverting buffer line driver line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has non-inverted outputs and two active-low output enables.

The HCT244A is the non-inverting version of the HCT240. See also HCT241.

Features

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1 μA
- In Compliance with the Requirements Defined by JEDEC Standard
- Chip Complexity: 112 FETs or 28 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant





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PDIP-20 N SUFFIX CASE 738



SOIC-20W DW SUFFIX CASE 751D



TSSOP-20 DT SUFFIX CASE 948E



SOEIAJ-20 M SUFFIX CASE 967

PIN ASSIGNMENT

1●	20	v _{cc}
2	19	ENABLE B
3	18	YA1
4	17] B4
5	16	YA2
6	15] B3
7	14	YA3
8	13] B2
9	12	YA4
10	11] B1
	2 3 4 5 6 7 8 9	2 19 3 18 4 17 5 16 6 15 7 14 8 13 9 12

FUNCTION TABLE

Inpu	Outputs	
Enable A, B		YA, YB
L	L	L
L	Н	Н
Н	X	Z

ORDERING AND MARKING INFORMATION

See detailed ordering, shipping, and marking information in the package dimensions section on page 5 of this data sheet.

Z = high impedance, X = don't care

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	– 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gua		Guaranteed Limit		imit	
Symbol	Parameter	Test Conditions	v _{cc}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit		
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	2 2	2 2	2 2	V		
V _{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V		
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V		
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6 \text{ mA}$	4.5	3.98	3.84	3.7			
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V		
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6 \text{ mA}$	4.5	0.26	0.33	0.4			
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ		
I _{OZ}	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH;}$ $V_{out} = V_{CC}$ or GND	5.5	± 0.5	± 5.0	± 10	μΑ		
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4	40	160	μΑ		
ΔI_{CC}	Additional Quiescent Supply	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ -55 °C	25°C to	125°C			
	Guiten	$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9	2	.4	mA		

^{1.} Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

[†]Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: – 7 mW/°C from 65° to 125°C

⁻ TSSOP Package: - 6.1 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS (V $_{CC}$ = 5.0 V \pm 10%, C_L = 50 pF, Input t_r = t_f = 6 ns)

		Gua	ranteed Limi	t	
Symbol	Parameter	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	20	25	30	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	26	33	39	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	22	28	33	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	12	15	18	ns
C _{in}	Maximum Input Capacitance	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V		Ī
C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	55	pF	

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

SWITCHING WAVEFORMS

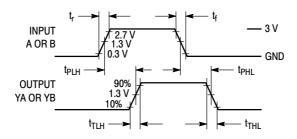


Figure 2.

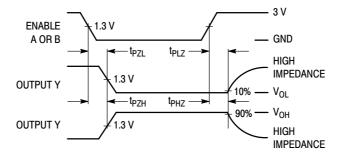
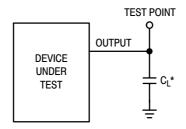


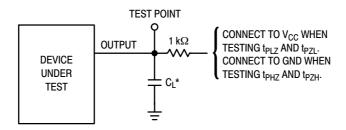
Figure 3.

TEST CIRCUITS



^{*}Includes all probe and jig capacitance

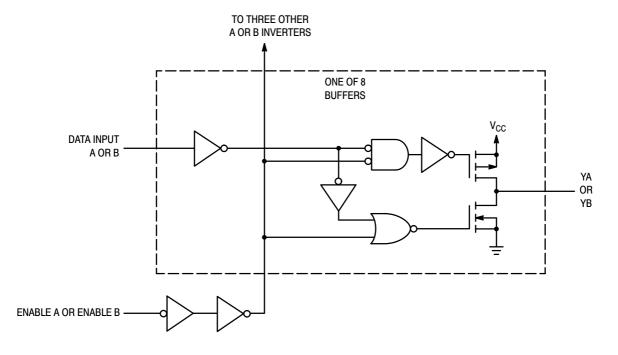
Figure 4.



*Includes all probe and jig capacitance

Figure 5.

LOGIC DETAIL

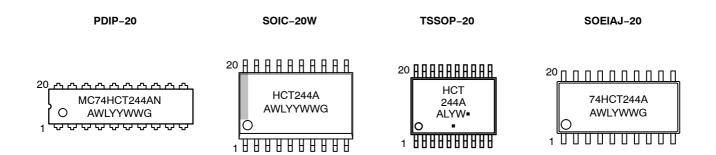


ORDERING INFORMATION

Device	Package	Shipping [†]	
MC74HCT244ANG	PDIP-20 (Pb-Free)	18 Units / Rail	
MC74HCT244ADWG	SOIC-20 (Pb-Free)	38 Units / Rail	
MC74HCT244ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel	
MC74HCT244ADTR2G	TSSOP-20*	2500 / Tape & Reel	
MC74HCT244AFG	SOEIAJ-20 (Pb-Free)	40 Units / Rail	
MC74HCT244AFELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS



A = Assembly Location

 $WL,\ L \quad = Wafer\ Lot$

YY, Y = Year

WW, W = Work Week

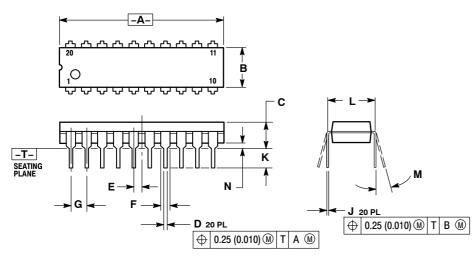
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

^{*}These packages are inherently Pb-Free.

PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E



NOTES:

- IOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

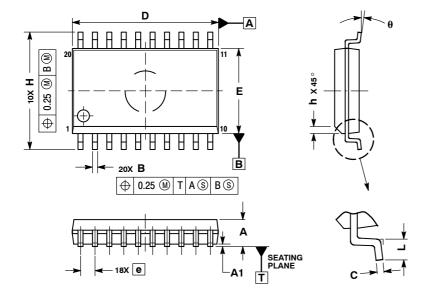
 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
Е	0.050	0.050 BSC		BSC
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

SOIC-20W **DW SUFFIX** CASE 751D-05 **ISSUE G**



NOTES:

- OTES:

 DIMENSIONS ARE IN MILLIMETERS.

 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 PROTRUSION.

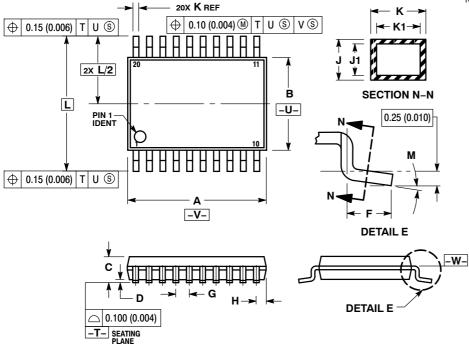
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
Δ.	00	70	

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 ISSUE C



16X 0.36

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. CONDITION.
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
M	0°	8°	0°	8°



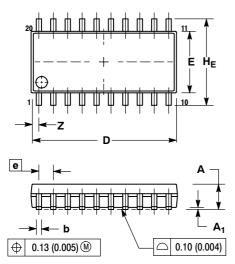
SOLDERING FOOTPRINT - 7.06

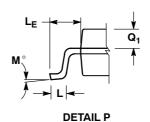
0.65

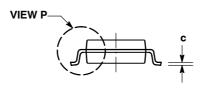
16X 1.26

PACKAGE DIMENSIONS

SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE A**







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AUTO . .
 Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
 MENSIONS D AND E DO NOT INCLUDE
 AND ARE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0°	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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